

2SK-182ES Specifications

ABSOLUTE MAXIMUM RATING (Ta=25°C)		
	Conditions	2SK-182ES
■ Storage Temperature		-50 ~ +150°C
■ Junction Temperature		+150°C
■ Gate - Source Voltage		70V
■ Gate - Drain Voltage		600V
■ Gate Current	VGS = 1V	0.5A
■ Drain Current		60A
■ Total power dissipation		500W
ELECTRICAL CHARACTERISTICS (Ta=25°C)		
■ Gate - Source breakdown voltage	IG = 0.1mA	70V min
■ Gate leakage current	VGS = -40V	100μA max
■ Off-condition Drain leakage current	VGS = -50V	100μA max
■ Drain current	VGS = 0	18A
	VDS = 10V	
■ Gate-Source Off-state voltage	VDS = 300V	30V
	ID = 1mA	
■ Gate-Drain breakdown voltage	ID = 0.1mA	600V min
■ Voltage amplification	VGS = -20V	10
	VDS = 0.1A	
■ Input capacitance	VGS = 10V	2500PF
	f = 1MHz	
■ Cutt-off frequency	VGS = 20V	10MHz
	ID = 2A	
■ Drain-Souce On-resistance	VGS = 0	0.3Ω max
	ID = 2A	
■ Drain-Souce Off-resistance	VDS = 300V	1MΩ min
	VGS = -50V	
■ Turn-on time	IGS = 1.5A	250ns
■ Turn-off time	VGS = 50V	300ns